

RJF0622JSP

60V, 3A N Channel Thermal FET Power Switching

R07DS1418EJ0100 Rev.1.00 Jun 04, 2018

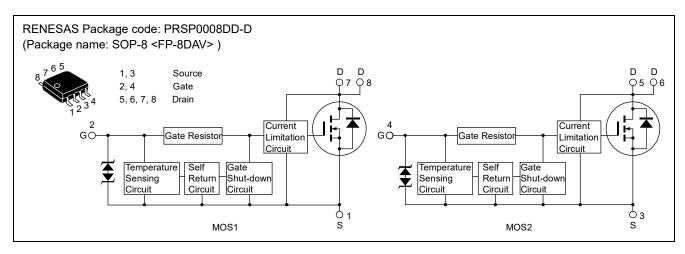
Description

This FET has the over temperature shut-down capability sensing to the junction temperature. This FET has the built-in over temperature shut-down circuit in the gate area. And this circuit operation to shut-down the gate voltage in case of high junction temperature like applying over power consumption, over current etc..

Features

- Logic level operation.
- Built-in the over temperature shut-down circuit and current limitation circuit.
- · High endurance capability against to the short circuit.
- Temperature hysteresis type.
- High density mounting
- Power supply voltage applies 12 V and 24 V. (Max Power supply voltage: 38 V)
- AEC-Q101 Compliant

Outline



Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

Item	Symbol	Ratings	Unit
Drain to source voltage	$V_{ extsf{DSS}}$	60	V
Gate to source voltage	V_{GSS}	16	V
Gate to source voltage	V_{GSS}	-2.5	V
Drain current	I _D Note4	3	Α
Body-drain diode reverse drain current	I _{DR}	3	Α
Avalanche current	I _{AP} Note 3	0.9	Α
Avalanche energy	E _{AR} Note 3	69.4	mJ
Channel dissipation	Pch Note 1	2	W
Channel dissipation	Pch Note 2	3	W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. 1 Drive operation: When using the glass epoxy board (FR4 $40 \times 40 \times 1.6$ mm), PW ≤ 10 s

- 2. 2 Drive operation: When using the glass epoxy board (FR4 $40 \times 40 \times 1.6$ mm), PW ≤ 10 s
- 3. Tch = 25°C, Rg \geq 50 $\Omega,$ L = 100 mH
- 4. It provides by the current limitation lower bound value.

Typical Operation Characteristics

 $(Ta = 25^{\circ}C)$

Item	Symbol	Min	Тур	Max	Unit	Test Conditions
Input voltage	VIH	3.5	_	_	V	
	VIL	_	_	1.2	V	
Input current	I _{IH1}	_	_	100	μА	Vi = 8 V, V _{DS} = 0
(Gate non shut down)	I _{IH2}	_	_	50	μА	Vi = 3.5 V, V _{DS} = 0
	I _{IL}	_	_	1	μА	Vi = 1.2 V, V _{DS} = 0
Input current	I _{IH(sd)1}	_	8.0	_	mA	Vi = 8 V, V _{DS} = 0
(Gate shut down)	I _{IH(sd)2}	_	0.35	_	mA	Vi = 3.5 V, V _{DS} = 0
Shut down temperature	Tsd	_	175	_	°C	Channel temperature
Return temperature	Thr	_	120	_	°C	Channel temperature
Gate operation voltage	Vop	3.5	_	12	V	
Drain current	I _{D limit}	3	_	_	Α	V _{GS} = 5 V, V _{DS} = 10 V Note 5
(Current limitation value)						
Load short-circuit voltage	V_{DD}	_	_	32	V	V _{GS} = 5 V, RL = 0

Notes: 5. Pulse test

Electrical Characteristics

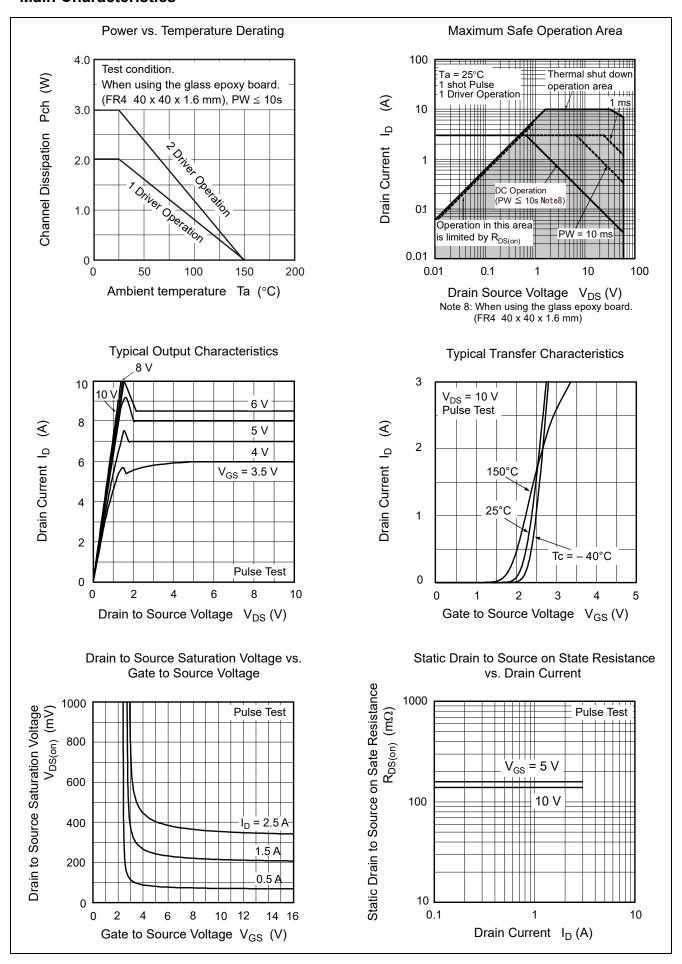
 $(Ta = 25^{\circ}C)$

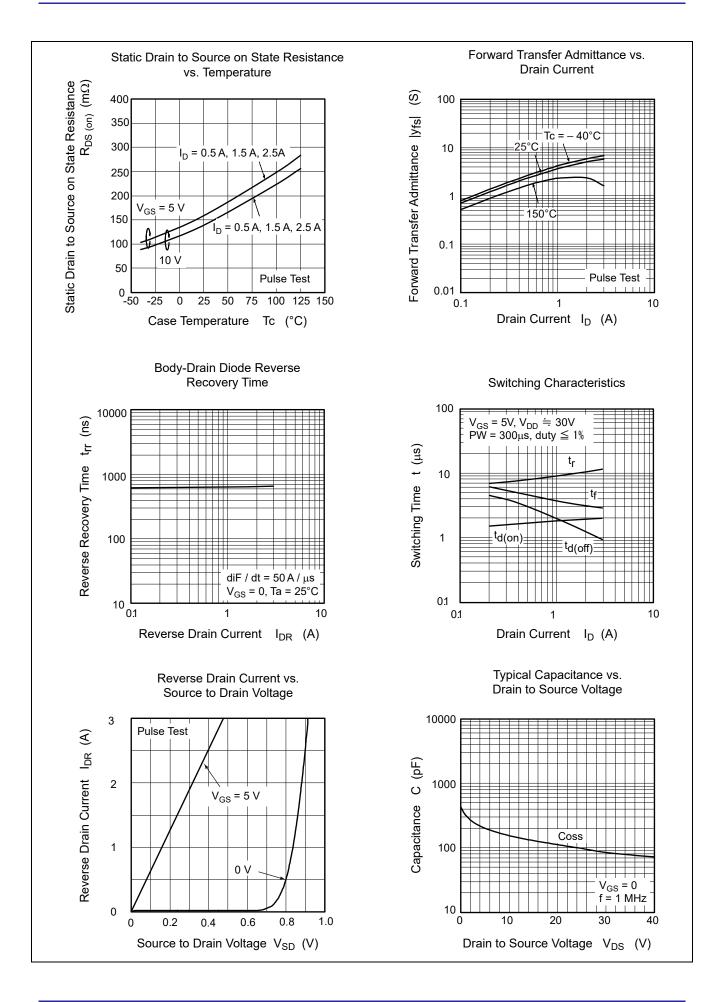
Item	Symbol	Min	Тур	Max	Unit	Test Conditions
Drain current	I _{D1}	_	_	10	mA	V _{GS} = 1.2 V, V _{DS} = 10 V
	I _{D2}	3	_	_	Α	V _{GS} = 5 V, V _{DS} =10 V Note 6
Drain to source breakdown voltage	V _{(BR)DSS}	60	_	80	V	I _D = 10 mA, V _{GS} = 0
Gate to source breakdown voltage	V _(BR) GSS	16	_	_	V	$I_G = 800 \mu A, V_{DS} = 0$
	V _(BR) GSS	-2.5	_	_	V	$I_G = -100 \mu A, V_{DS} = 0$
Gate to source leak current	Igss ₁	_	_	100	μΑ	V _{GS} = 8 V, V _{DS} = 0
	I _{GSS2}	_	_	50	μА	V _{GS} = 3.5 V, V _{DS} = 0
	Igss3	_	_	1	μА	V _{GS} = 1.2 V, V _{DS} = 0
	I _{GSS4}	_	_	-100	μА	V _{GS} = -2.4 V, V _{DS} = 0
Input current (shut down)	I _{GS(OP)1}	_	0.8	_	mA	V _{GS} = 8 V, V _{DS} = 0
	I _{GS(OP)2}	_	0.35	_	mA	V _{GS} = 3.5 V, V _{DS} = 0
Zero gate voltage drain current	I _{DSS}	_	_	10	μА	V _{DS} = 32 V, V _{GS} = 0,
						Ta = 125°C
Gate to source cutoff voltage	$V_{GS(off)}$	1.1	_	2.1	V	$I_D = 1 \text{ mA}, V_{DS} = 10 \text{ V}$
Static drain to source on state	R _{DS(on)}	_	159	180	mΩ	$I_D = 2.5 \text{ A}, V_{GS} = 5 \text{ V}^{\text{Note 6}}$
resistance	R _{DS(on)}	_	139	160	mΩ	$I_D = 2.5 \text{ A}, V_{GS} = 10 \text{ V}^{\text{Note 6}}$
Forward transfer admittance	y _{fs}	3.3	5.4	_	S	$I_D = 2.5 \text{ A}, V_{DS} = 10 \text{ V}^{\text{Note 6}}$
Output capacitance	Coss	_	154	_	pF	$V_{DS} = 10 \text{ V}, V_{GS} = 0, f = 1 \text{MHz}$
Turn-on delay time	t _{d(on)}	_	1.9	_	μs	I _D = 2.5 A
Rise time	t _r	_	11.0	_	μs	$V_{GS} = 5 V$,
Turn-off delay time	$t_{d(off)}$	_	1.1	_	μS	$R_L = 12 \Omega$
Fall time	t _f	_	3.0	_	μS	
Body-drain diode forward voltage	V_{DF}	_	0.91	_	V	$I_F = 5 A, V_{GS} = 0$
Body-drain diode reverse recovery	t _{rr}	_	662	_	ns	I _F = 3 A, V _{GS} = 0
time						di _F /dt = 50 A/μs
Over load shut down	t _{os1}	_	0.29	_	ms	$V_{GS} = 5 \text{ V}, V_{DD} = 16 \text{ V}$
operation time Note 7	t _{os2}	_	0.18	_	ms	$V_{GS} = 5 \text{ V}, V_{DD} = 24 \text{ V}$

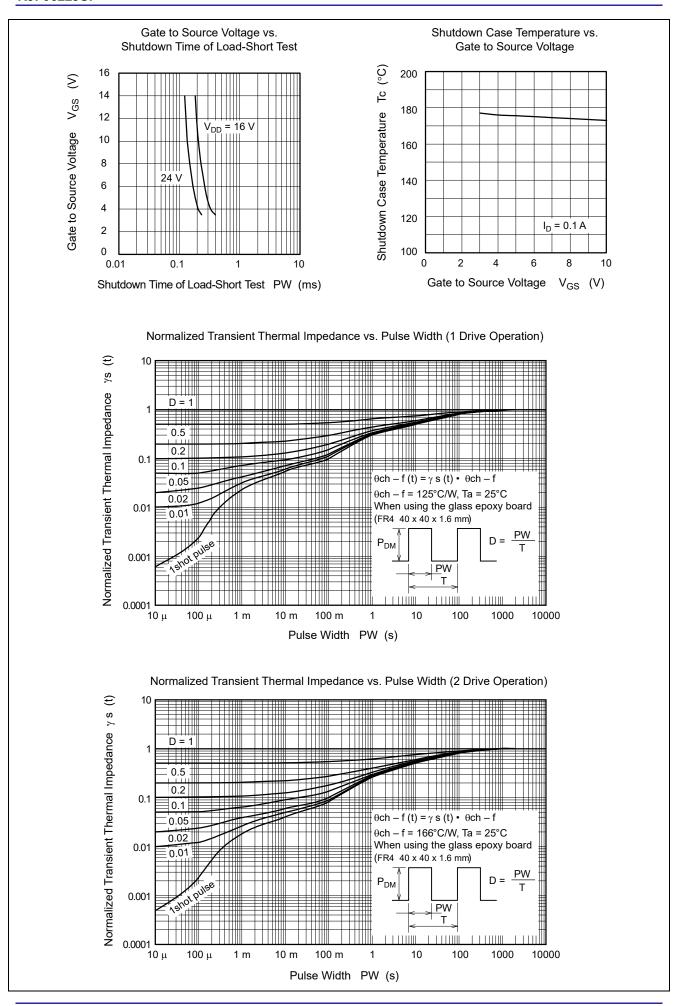
Notes: 6. Pulse test

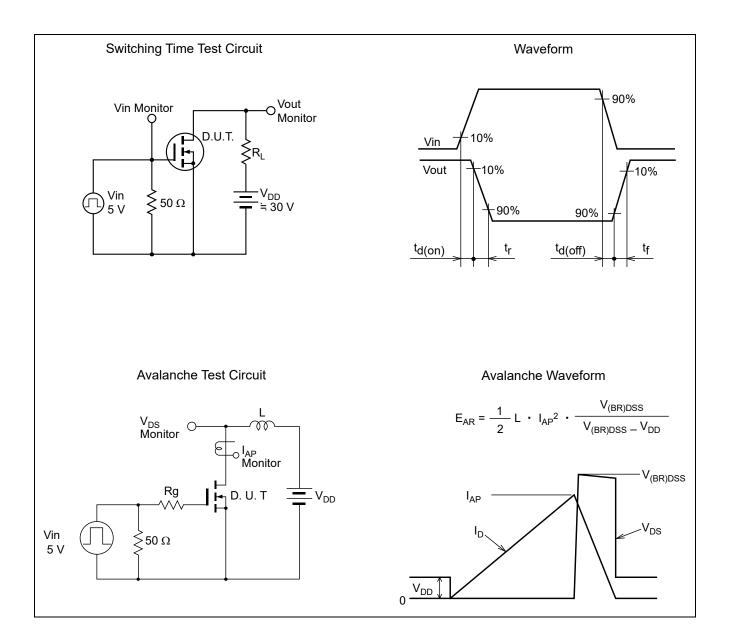
7. Including the junction temperature rise of the over loaded condition.

Main Characteristics

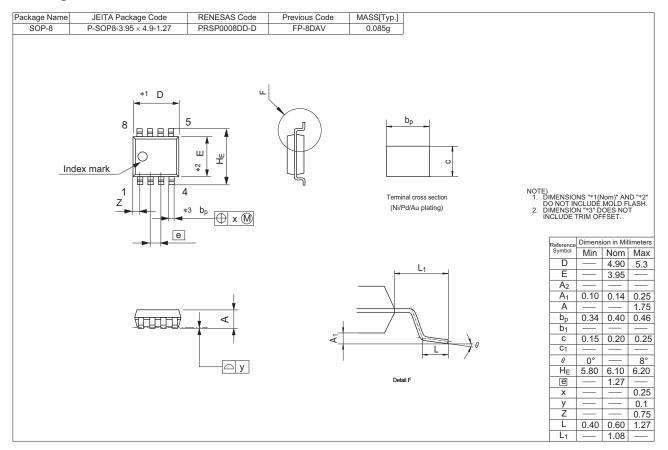








Package Dimensions



Ordering Information

Orderable Part Number	Quantity	Shipping Container
RJF0622JSP-00-J0	2500 pcs/Reel	Taping (Reel)

Note: The symbol of 2nd "-" is occasionally presented as "#".

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(Rev.4.0-1 November 2017)



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